

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1. (original) An active matrix type liquid crystal display device having a structure in which a pixel TFT is disposed in a trench carved in a substrate; wherein

with a section which is not carved in but left hill-shaped being present in the vicinity of the TFT, an underneath light-shielding film disposed beneath a semiconductor layer of the TFT is formed so as to reach at least the top of said hill-shaped section; and a metal electrode layer formed above the semiconductor layer of the TFT extends to the top of said hill-shaped section; and besides, on the top of said hill-shaped section, a film thickness of an interlayer insulating film laid between said underneath light-shielding film and metal electrode layer is made thinner than in other sections thereof.

2. (original) A liquid crystal display device according to Claim 1; wherein the interlayer insulating film laid between said underneath light-shielding film and metal electrode layer comprises a first interlayer film formed between the underneath light-shielding film and the semiconductor layer as

well as a gate insulating film formed between the semiconductor layer and the metal electrode layer; and, on the top of said hill-shaped section, at least a part of said first interlayer film in the direction of the thickness is etched away.

3. (original) A liquid crystal display device according to Claim 2, wherein, after said first interlayer film is removed to expose the light-shielding metal film on the top of said hill-shaped section, a second interlayer film which is thinner than said first interlayer film is formed, and thereafter the gate insulating film is formed.

4. (original) A liquid crystal display device according to Claim 1, wherein said hill-shaped section is formed so as to enclose the TFT.

5. (original) A liquid crystal display device according to Claim 1, wherein said hill-shaped section is formed on either side of a region where the semiconductor layer of the TFT is formed in the direction parallel to a gate line so that said region may become groove-shaped.

6. (original) A liquid crystal display device according to Claim 4, wherein a portion of said semiconductor layer of the TFT constitutes a storage capacitor section and the interlayer film laid between the semiconductor layer and the underneath light-shielding film in said storage capacitor section is made thinner than in the TFT section.

7. (original) A liquid crystal display device according to Claim 5, wherein a portion of said semiconductor layer of the TFT constitute a storage capacitor section and the interlayer film laid between the semiconductor layer and the underneath light-shielding film in said storage capacitor section is made thinner than in the TFT section.

8-21. (canceled).